EAST - [resistor.wsp:1]

File View Edit Tools Window Help

- Drafts
- Pending
- Active
  - L1: (105747) nonvolatile or (non adj volatile
  - L2: (4626) 1 and (floating adj gate).clm.
  - L3: (829) 2 and (second near (floating adj ga
  - L4: (380) 3 and (second adj floating)
  - L5: (197) 4 and (dielectric)
  - L6: (94) 5 and ((side adj wall) or sidewall)
  - L7: (83) 6 and (opening$1 or via$1 or trench$
  - L8: (31) 7 and (opening$1 or via$1 or trench$
  - L9: (16) 1 and (second adj2 floating adj2 por
- Failed

DBs: USPAT; US-PGPUB

1 and (second adj2 floating adj2 portion$1)

#	U	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C				
1	☐	☐	☐	US 20040036108	20040226	18	High coupling floating gate transistor	257/314			Rudeck, Paul	☑	☐	☐	☐	☑	☐
2	☑	☐	☐	US 20040036106	20040226	18	HIGH COUPLING FLOATING GATE TRANSISTOR	257/314			Rudeck, Paul	☑	☐	☐	☐	☐	☐
3	☐	☐	☐	US 20030141538	20030731	18	Semiconductor device, nonvolatile semiconduct	257/315	257/E21.682;		Hayashi, Fumihiko	☑	☐	☐	☐	☐	☐
4	☐	☐	☐	US 20010015920	20010823	20	Flash eprom memory cell having increased capaci	365/200	257/E21.209;		Ratnam, Perumal et al.	☑	☐	☐	☐	☐	☐
5	☐	☐	☐	US 20010003366	20010614	19	Semiconductor device, nonvolatile semiconduct	257/315	257/E21.682;		Hayashi, Fumihiko	☑	☐	☐	☐	☐	☐
6	☑	☐	☐	US 6525962 B1	20030225	9	High current and/or high speed electrically	365/185.09	257/314; 257/315;		Pai, Sheng-Yueh et al.	☑	☐	☐	☐	☐	☐
7	☑	☐	☐	US 6243293 B1	20010605	21	Contacted cell array configuration for erasa	365/185.14	365/185.15;		Van Houdt, Jan F. et al.	☑	☐	☐	☐	☐	☐
8	☐	☐	☐	US 6115285 A	20000905	21	Device and method for multi-level charge/stor	365/185.03	365/185.2; 365/185.26		Montanari, Donato et al.	☑	☐	☐	☐	☐	☐
9	☐	☐	☐	US 6009013 A	19991228	26	Contactless array configuration for semic	365/185.14	365/185.15;		Van Houdt, Jan F. et al.	☑	☐	☐	☐	☐	☐
10	☐	☐	☐	US 5981338 A	19991109	10	High density flash memory	438/257	438/593		Lee, Roger R.	☑	☐	☐	☐	☐	☐
11	☐	☐	☐	US 5936275 A	19990810	9	High density flash memory cell and method	257/315	257/316; 257/366;		Lee, Roger R.	☑	☐	☐	☐	☐	☐
12	☐	☐	☐	US 5841161 A	19981124	11	Flash memory and method for fabricating the sam	257/315	257/321; 257/E21.20		Lim, Min Gye et al.	☑	☐	☐	☐	☐	☐
13	☑	☐	☐	US 5583810 A	19961210	13	Method for programming a semiconductor memory	365/185.15	257/319; 257/320;		Van Houdt, Jan et al.	☑	☐	☐	☐	☐	☐
14	☐	☐	☐	US 5410799 A	19950502	18	Method of making electrostatic switches	29/622	200/181; 29/829		Thomas, Michael E.	☑	☐	☐	☐	☐	☐
15	☐	☐	☐	US 5389567 A	19950214	9	Method of forming a non-volatile DRAM cell	438/594	438/251; 438/264;		Acovic, Alexandre et al.	☑	☐	☐	☐	☐	☐
16	☐	☐	☐	US 4672580 A	19870609	13	Memory cell providing simultaneous non-destru	365/185.08	257/321; 365/185.1;		Yau, Robert L. et al.	☑	☐	☐	☐	☐	☐

Ready